

109. ✓ A method according to claim 25, wherein an exposed surface of said crystallized semiconductor film is oxidized by said oxidizing.

110. ✓ A method according to claim 33, wherein an exposed surface of said crystallized semiconductor film is oxidized by said oxidizing.

111. ✓ A method according to claim 41, wherein an exposed surface of said crystallized semiconductor film is oxidized by said oxidizing.

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enc 112. ✓ A method according to claim 49, wherein an exposed surface of said crystallized semiconductor film is oxidized by said oxidizing.

113. ✓ A method according to claim 56, wherein an exposed surface of said crystallized semiconductor film is oxidized by said oxidizing.

114. ✓ A method according to claim 63, wherein an exposed surface of said crystallized semiconductor film is oxidized by said oxidizing.

115. ✓ A method according to claim 70, wherein an exposed surface of said crystallized semiconductor film is oxidized by said oxidizing.

116. ✓ A method according to claim 78, wherein an exposed surface of said crystallized semiconductor film is oxidized by said oxidizing.

117. ✓ A method according to claim 86, wherein an exposed surface of said crystallized semiconductor film is oxidized by said oxidizing.--
